Preface

This issue of ECS Transactions includes 23 papers that were presented at the Fifth International Conference on Semiconductor Technology for Ultra Large Integrated Circuits and Thin Film Transistors (ULSIC vs. TFT 5), held in Tahoe City, CA, from June 15-18, 2015. This symposium was sponsored by the Engineering Conferences International.

Following the tradition of the last four conferences, this is a forum for the open discussion on the latest progress of the two largest semiconductor technologies - ULSIC and TFT. Global experts from universities, companies, and national laboratories exchanged experience, knowledge, and visions through technical presentations and discussions. Participants and authors were from France, Germany, India, Japan, Korea, Saudi Arabia, Taiwan, UK, and USA.

There were two plenary speeches dedicated to “Solving the Metallization Challenges in Semiconductor Manufacturing” by S. Ramamurthy of Applied Materials Inc. and “Wide band gap semiconductors transistors for power devices and FPD” by E.-S. Nam of ETRI. The conference also included two panel sessions on 1) challenges in oxide applications in IC, displays, etc. and 2) challenges in nano transistors. In total, 43 papers were presented during the following sessions:

- Plenary
- Oxide TFTs
- Memories and materials
- Oxide TFT fabrications
- Etching & Deposition Processes
- Oxide and Si TFTs and GaN
- New Devices
- New Devices Applications
- Posters

In order to present subjects in a coherent manner, papers in this issue of ECS Transactions have been arranged into six chapters. All manuscripts are published as originally received, without alteration of technical content, except minor formatting corrections.

The success of this conference is contributed by the following people and organizations:

- Plenary, invited, oral, and poster speakers for presentations and panel discussions
- Session chairs for conducting the meeting
- Scientific advisory committee members for contributions in planning and discussions.
- Dr. N. Li for valuable advice as the conference ECI liaison
- ECI staff for effective management of the conference
- Beth Anne Stuebe of ECS for publishing this ECS Transactions volume

Yue Kuo
Texas A&M University
Acknowledgement

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S. Yamazaki, Semiconductor Energy Laboratory
Y. Zhang, Applied Materials
# Table of Contents

*Preface*  

### Chapter 1  
**Oxide TFT Devices**

- (Invited) Advances in Oxide Thin-Film Transistors in Recent Decade and Their Future  
  *H. Kumomi, T. Kamiya, H. Hosono*  
  3

- (Invited) Reliability Enhancement of High-Mobility Amorphous Indium-Tungsten Oxide Thin Film Transistor  
  *P. T. Liu, C. H. Chang, C. J. Chang*  
  9

- Analysis for Extremely Low Off-State Current in CAAC-IGZO FETs  
  *M. Tsubuku, D. Matsubayashi, T. Takeuchi, R. Honda, T. Murakawa, S. Matsuda, Y. Yamamoto, S. Yamazaki*  
  17

- The Stability of Noise Behavior in Amorphous Indium Gallium Zinc Oxide Thin Film Transistors under Illumination  
  *C. Y. Chang, Y. H. Tai*  
  23

### Chapter 2  
**Oxide TFT Materials and Fabrication**

- (Invited) The Behavior of C-axis-aligned A-b-plane-anchored Crystal (CAA Crystal)  
  *S. Yamazaki*  
  29

- (Invited) Doping and Defect Passivation in In-Ga-Zn-O by Fluorine  
  *M. Furuta, J. Jiang, G. Tatsuoka, D. Wang*  
  41

- (Invited) Solution-process Oxide TFTs for Hybrid Low-Voltage CMOS Applications  
  *Y. Hong, S. B. Ji, H. Im, N. Seong, Y. Park, H. Kim*  
  51
Chapter 3
Si TFTs

(Invited) Integrated Gate Driver Circuits Using a-Si TFT and Oxide TFT
   Y. H. Jang, S. C. Choi, B. Kim, J. U. Bae, K. S. Park
61

High Current Stress-Induced Heating Effects in Thin-Film Transistors on Plastic:
   Oxide Vs. Ltps
   S. Lee, M. Mativenga, J. Jang
73

(Invited) High-Performance Top-Gate and Double-Gate Low-Temperature
   Polycrystalline-Silicon Thin-Film Transistors Fabricated Using
   Continuous-Wave-Laser Lateral Crystallization on a Glass Substrate
   A. Hara, T. Meguro, S. Sasaki, H. Ohsawa
79

Bulk Barrier Source-Gated Transistors with Improved Drain Current Dynamic Range
   and Temperature Coefficient
   R. A. Sporea, W. Wright, J. M. Shannon, S. R. P. Silva
91

Chapter 4
Memories and Materials

(Invited) Metal-Insulator-Metal Devices with High-K Dielectric for Nonvolatile or
   Dynamic Random Access Memories
   A. Bsiesy Sr., P. Gonon Sr., C. Vallée Sr., J. Pointet Jr., C. Mannequin Jr.
99

Chapter 5
Ge Technology and Devices

(Invited) Opportunities of High Performance Ge CMOS
   A. Toriumi
113

(Invited) Advanced Germanium Epitaxy for Photonics Application
   Y. Yamamoto, S. Lischke, L. Zimmermann, D. Knoll, J. Murota, B. Tillack
123

(Invited) Atomically Controlled Processing for Germanium-Based CVD Epitaxial
   Growth
   J. Murota, Y. Yamamoto, B. Tillack
135

viii
Chapter 6
New Devices and Applications

(Invited) The Multidisciplinary Approach: A Common Trend for ULSI and Thin Film Technology
O. Bonnaud

(Plenary) Wide Band Gap Semiconductor Transistors for FPD
C. S. Hwang, E. S. Nam

(Invited) Graphene Heat Spreaders and Interconnects for Advanced Electronic Applications
A. Balandin

(Invited) Hetero Interface of Ionic/Covalent Oxides for Nano-Electronics
T. Nabatame

(Invited) A Diode-Like Antifuse Device Made of High-K Dielectric
Y. Kuo

(Invited) Wavy Channel TFT Architecture for High Performance Oxide Based Displays

An Organic Device with Thin Film Transistor Merged with Light Emitting Diode through Use of an Accumulation Layer in TFT As an Electrode
A. Gangwar, B. Mazhari

(Invited) Leakage Current Reduction in ALD-Al₂O₃ Dielectric Deposited on Si by High Pressure Deuterium Oxide Annealing
K. Yoshitsugu, M. Horita, Y. Ishikawa, Y. Uraoka

Author Index
Facts about ECS

The Electrochemical Society (ECS) is an international, nonprofit, scientific, educational organization founded for the advancement of the theory and practice of electrochemistry, electronics, and allied subjects. The Society was founded in Philadelphia in 1902 and incorporated in 1930. There are currently over 7,000 scientists and engineers from more than 70 countries who hold individual membership; the Society is also supported by more than 100 corporations through Corporate Memberships.

The technical activities of the Society are carried on by Divisions. Sections of the Society have been organized in a number of cities and regions. Major international meetings of the Society are held in the spring and fall of each year. At these meetings, the Divisions and Groups hold general sessions and sponsor symposia on specialized subjects.

The Society has an active publication program that includes the following:

*Journal of The Electrochemical Society* — (JES) is the leader in the field of electrochemical science and technology. This peer-reviewed journal publishes an average of 550 pages of 85 articles each month. Articles are published online as soon as possible after undergoing the peer-review process. The online version is considered the final version and is fully citable with articles assigned specific page numbers within specific issues. The date of online publication is the official publication date of record.

*Journal of Solid State Science and Technology* — (JSS) is one of the newest peer-reviewed journals from ECS launched in 2012. JSS covers fundamental and applied areas of solid state science and technology including experimental and theoretical aspects of the chemistry and physics of materials and devices. Articles are published online as soon as possible after undergoing the peer-review process. The online version is considered the final version and is fully citable with articles assigned specific page numbers within specific issues. The date of online publication is the official publication date of record.

*Electrochemistry Letters* — (EEL) is one of the newest journals from ECS launched in 2012. It is dedicated to the rapid dissemination of peer-reviewed and concise research reports in fundamental and applied areas of electrochemical science and technology. Articles are published online as soon as possible after undergoing the peer-review process. The online version is considered the final version and is fully citable with articles assigned specific page numbers within specific issues. The date of online publication is the official publication date of record.

*Solid State Letters* — (SSL) is one of the newest journals from ECS launched in 2012. It is dedicated to the rapid dissemination of peer-reviewed and concise research reports in fundamental and applied areas of solid state science and technology. Articles are published online as soon as possible after undergoing the peer-review process. The online version is considered the final version and is fully citable with articles assigned specific page numbers within specific issues. The date of online publication is the official publication date of record.

*Electrochemical and Solid-State Letters* — (ESL) was the first rapid-publication electronic journal dedicated to covering the leading edge of research and development in the field of solid-state and electrochemical science and technology. ESL was a joint publication of ECS and IEEE Electron Devices Society. Volume 1 began July 1998 and contained six issues, thereafter new volumes began with the January issue and contained 12 issues. The final issue of ESL was Volume 16, Number 6, 2012. Preserved as an archive, ESL has since been replaced by SSL and EEL.

*Interface* — Interface is an authoritative yet accessible publication for those in the field of solid-state and electrochemical science and technology. Published quarterly, this four-color magazine contains technical articles about the latest developments in the field, and presents news and information about and for members of ECS.

*ECS Meeting Abstracts* — ECS Meeting Abstracts contain extended abstracts of the technical papers presented at the ECS biannual meetings and ECS-sponsored meetings. This publication offers a first look into the current research in the field. ECS Meeting Abstracts are freely available to all visitors to the ECS Digital Library.

*ECS Transactions* — (ECST) is the online database containing full-text content of proceedings from ECS meetings and ECS-sponsored meetings. ECST is a high-quality venue for authors and an excellent resource for researchers. The papers appearing in ECST are reviewed to ensure that submissions meet generally-accepted scientific standards. Each meeting is represented by a volume and each symposium by an issue.

Monograph Volumes — The Society sponsors the publication of hardbound monograph volumes, which provide authoritative accounts of specific topics in electrochemistry, solid-state science, and related disciplines.

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